



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Application of

Shunpei YAMAZAKI et al.

Serial No. 09/362,192

Filed: July 28, 1999

For: SEMICONDUCTOR DEVICE

HAVING SEMICONDUCTOR CIRCUIT

COMPRISING SEMICONDUCTOR

ELEMENT, AND METHOD FOR

MANUFACTURING THE SAME

) Art Unit: 2812

) Examiner: V. Simkovic

CERTIFICATE OF MAILING

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AMENDMENT

Honorable Commissioner of Patents

Washington, D.C. 20231

Sir:

In response to the Office Action dated May 14, 2002, please amend the above-identified application as follows:

IN THE CLAIMS: ✓

Please cancel claims 51, 55, 59, 63 and 66 and amend claims 45, 49, 52, 56, 60 and 64 as follows:

45. (Amended) A method for manufacturing a semiconductor device comprising steps of:

providing a material for promoting crystallization to at least a part of a semiconductor film formed over a substrate;

subjecting said semiconductor film to oxygen plasma to form a gate insulating film on said semiconductor film; and

crystallizing said semiconductor film after subjecting said semiconductor film to the oxygen plasma to obtain a crystalline semiconductor film.

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